

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	12mΩ @ V <sub>GS</sub> = 10V	80A
	18mΩ @ V <sub>GS</sub> = 4.5V	70A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

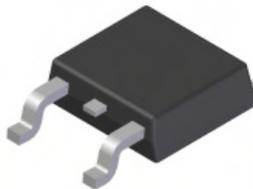
- Engine Management Systems
- Body Control Electronics
- DC/DC Converters

## Features

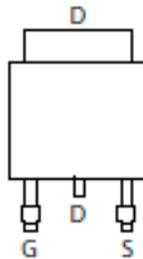
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures more Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

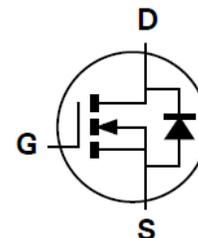
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 **e3**
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



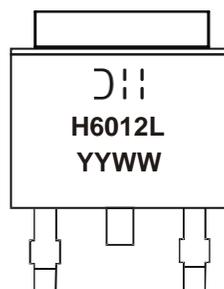
Equivalent Circuit

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH6012LK3Q-13	TO252 (DPAK)	2500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



**D** = Manufacturer's Marking  
**H6012L** = Product Type Marking Code  
**YYWW** = Date Code Marking  
**YY** = Last Two Digits of Year (ex: 16 = 2016)  
**WW** = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 8), V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	80
		T <sub>C</sub> = +100°C	60
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	120	A
Maximum Continuous Body Diode Forward Current (Note 8)	I <sub>S</sub>	80	A
Avalanche Current, L = 0.1mH (Note 9)	I <sub>AS</sub>	45	A
Avalanche Energy, L = 0.1mH (Note 9)	E <sub>AS</sub>	100	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	74	°C/W
	Steady State		
Total Power Dissipation (Note 7)	P <sub>D</sub>	3.8	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	40	°C/W
	Steady State		
Thermal Resistance, Junction to Case (Note 8)	R <sub>θJC</sub>	1.2	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 10)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 10)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	8	12	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A
		—	10	18		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A
<b>DYNAMIC CHARACTERISTICS (Note 11)</b>						
Input Capacitance	C <sub>iss</sub>	—	1926	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	330	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	112	—	pF	
Gate Resistance	R <sub>g</sub>	—	2.0	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	16.3	—	nC	
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	35.2	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 25A
Gate-Source Charge	Q <sub>gs</sub>	—	7.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	6.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.4	—	ns	
Turn-On Rise Time	t <sub>R</sub>	—	11.9	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V, R <sub>g</sub> = 3Ω, I <sub>D</sub> = 25A
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	16.5	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	5	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	28	—	ns	I <sub>F</sub> = 25A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	23	—	nC	I <sub>F</sub> = 25A, di/dt = 100A/µs

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  8. Thermal resistance from junction to soldering point (on the exposed drain pad).
  9. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  10. Short duration pulse test used to minimize self-heating effect.
  11. Guaranteed by design. Not subject to product testing.

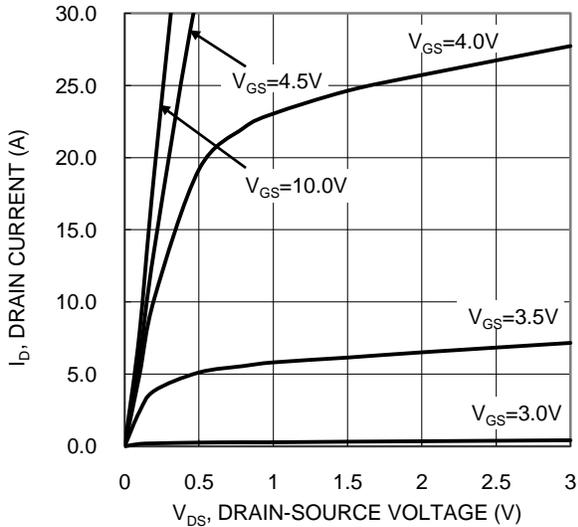


Figure 1. Typical Output Characteristic

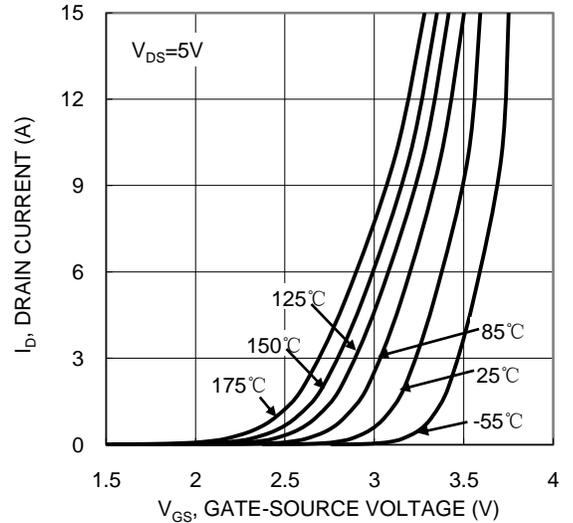


Figure 2. Typical Transfer Characteristic

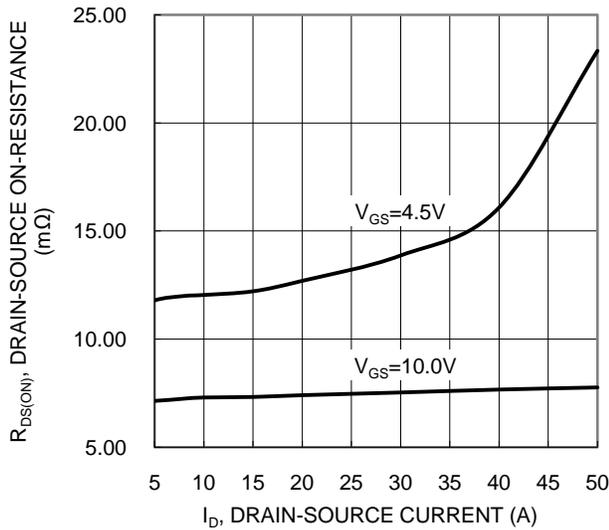


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

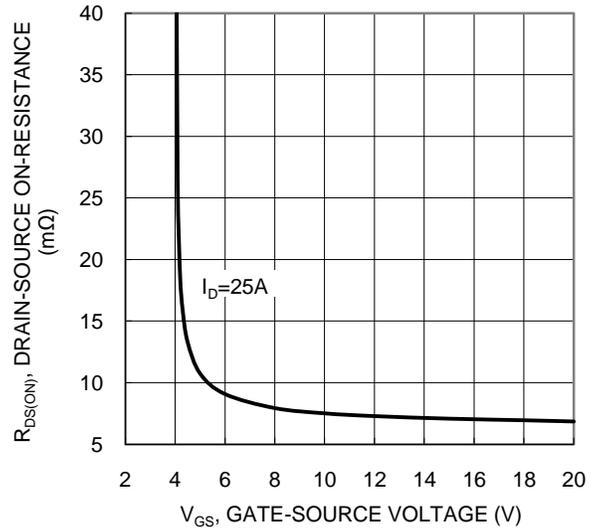


Figure 4. Typical Transfer Characteristic

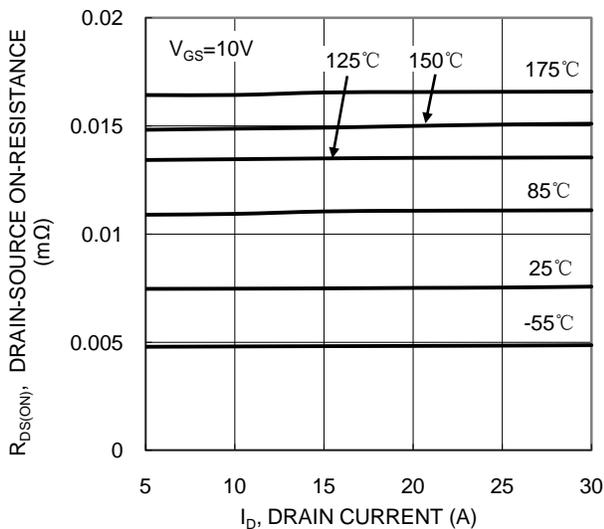


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

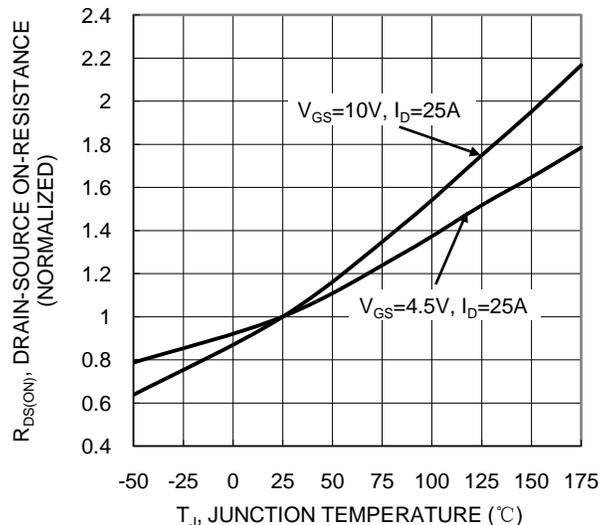


Figure 6. On-Resistance Variation with Temperature

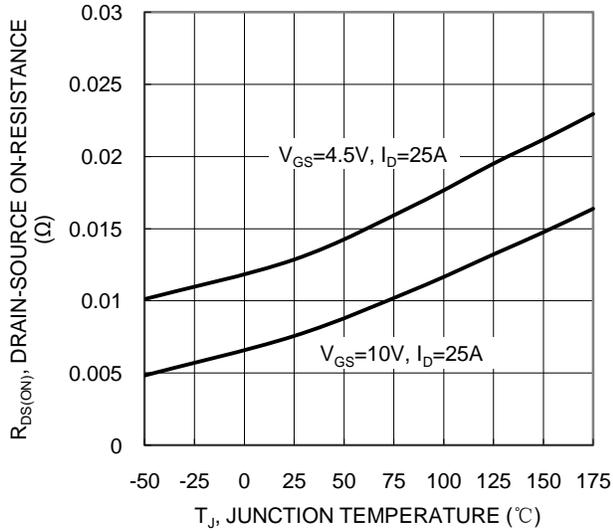


Figure 7. On-Resistance Variation with Temperature

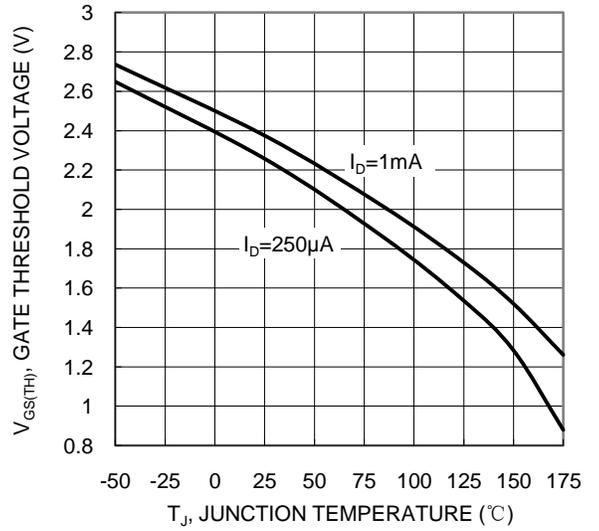


Figure 8. Gate Threshold Variation vs. Junction Temperature

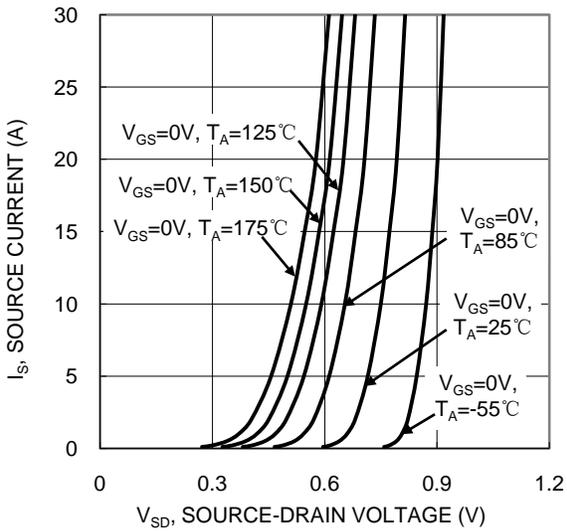


Figure 9. Diode Forward Voltage vs. Current

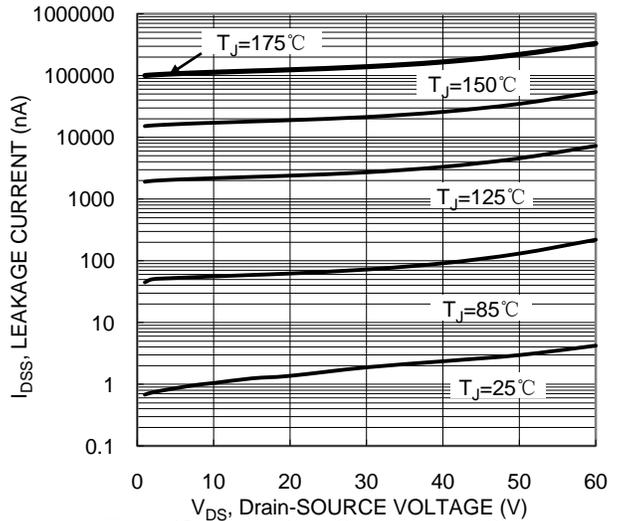


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

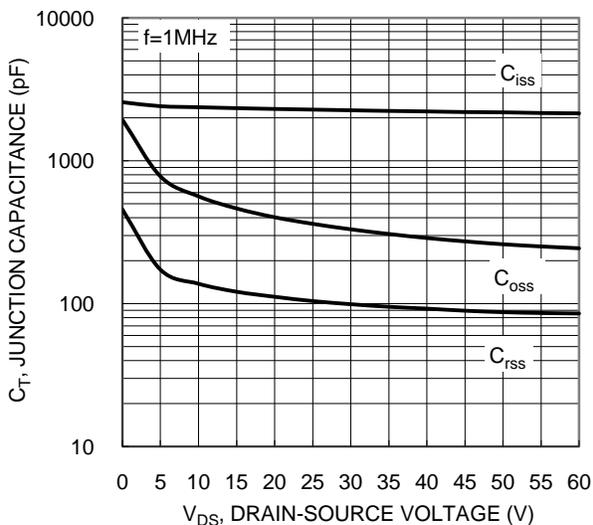


Figure: 11. Typical Junction Capacitance

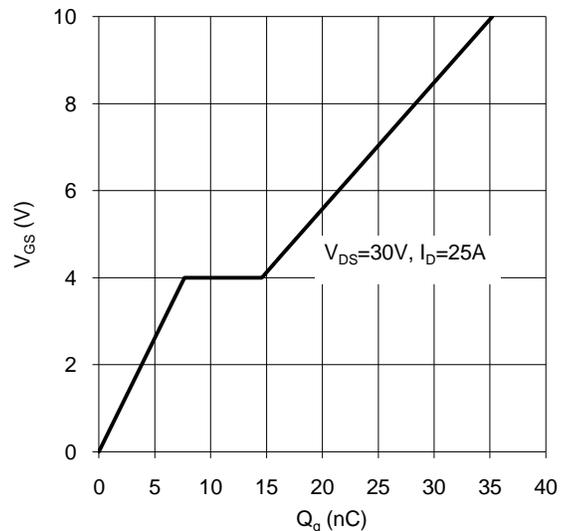


Figure 12. Gate Charge

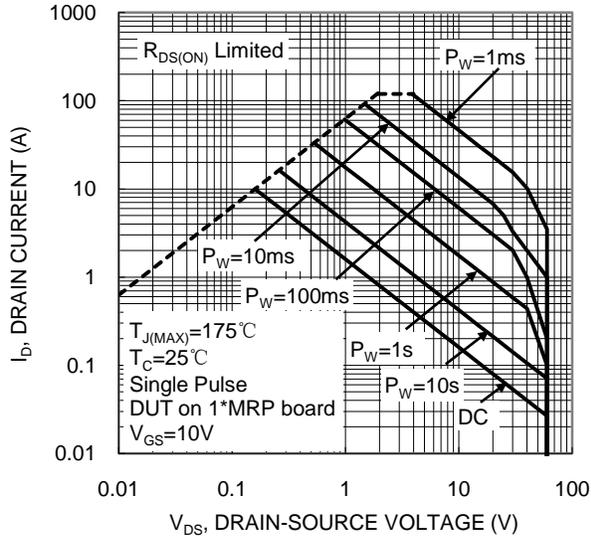


Figure 13. SOA, Safe Operation Area

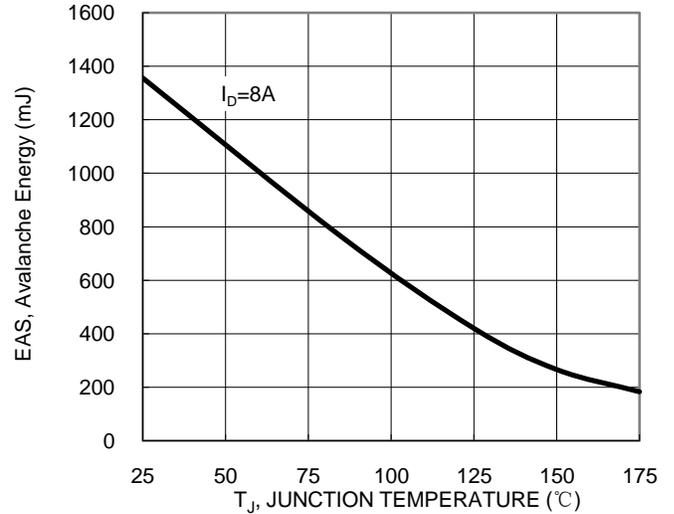


Figure 14. Avalanche Energy vs. Junction Temperature

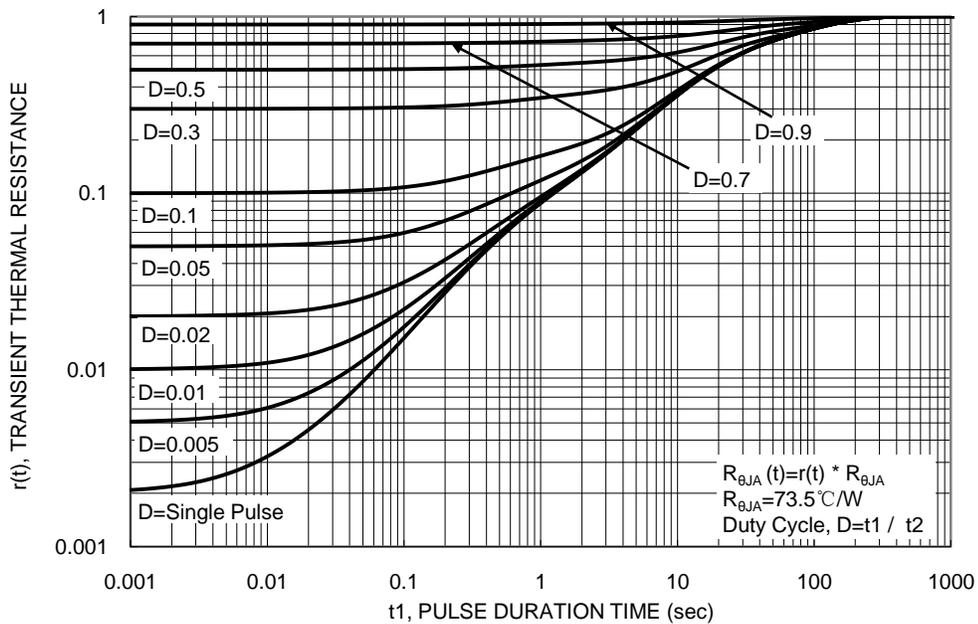
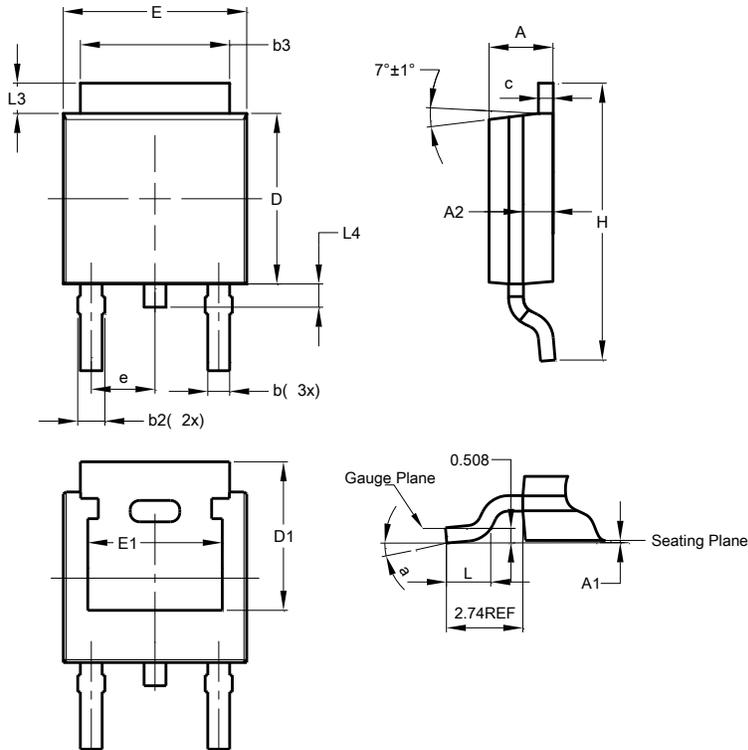


Figure 15. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

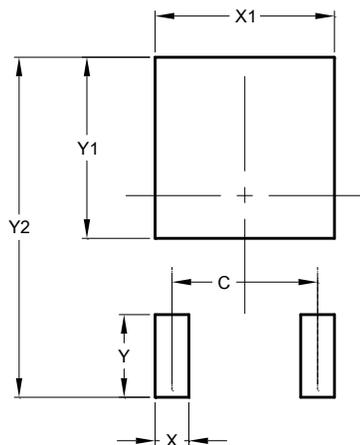


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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